











TLV313, TLV2313, TLV4313

SBOS753B - JUNE 2016-REVISED FEBRUARY 2017

TLVx313 Low-Power, Rail-to-Rail In/Out, 500-µV Typical Offset, 1-MHz Operational Amplifier for Cost-Sensitive Systems

Features

Precision Amplifier for Cost-Sensitive Systems

Low Io: 65 µA/ch

Wide Supply Range: 1.8 V to 5.5 V Low Noise: 26 nV/√Hz at 1 kHz

Gain Bandwidth: 1 MHz Rail-to-Rail Input/Output Low Input Bias Current: 1 pA Low Offset Voltage: 0.75 mV

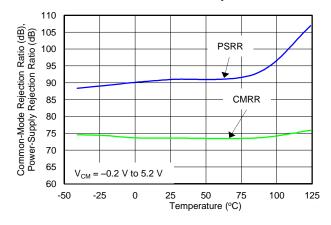
Unity-Gain Stable Internal RF/EMI Filter

Extended Temperature Range: -40°C to +125°C

2 Applications

- Medical and Healthcare
- Fitness and Wearable Electronics
- Utility Metering (Heat, Water, Energy)
- **Building Automation Equipment**
- **Currency Counters**

CMRR and **PSRR** vs Temperature



3 Description

The TLV313 family of single-, dual-, and quadchannel precision operational amplifiers combine low power consumption with good performance. This makes them suitable for a wide range of applications, as wearables, utility metering, building automation, currency counters and more. The family features rail-to-rail input and output (RRIO) swings, low quiescent current (65 µA, typical), wide bandwidth (1 MHz) and very low noise (26 nV/√Hz at 1 kHz), making it attractive for a variety of battery-powered applications that require a good balance between cost and performance. Further, low-input-bias current enables these devices to be used in applications with megaohm source impedances.

The robust design of the TLV313 devices provides ease-of-use to the circuit designer: unity-gain stability with capacitive loads of up to 150 pF, integrated RF/EMI rejection filter, no phase reversal in overdrive conditions, and high electrostatic discharge (ESD) protection (4-kV HBM).

The devices are optimized for operation at voltages as low as $+1.8 \text{ V} (\pm 0.9 \text{ V})$ and up to $+5.5 \text{ V} (\pm 2.75 \text{ V})$, and are specified over the extended temperature range of -40°C to +125°C.

The single-channel TLV313 device is available in both SC70-5 and SOT23-5 packages. The dualchannel TLV2313 device is offered in SOIC-8 and VSSOP-8 packages, and the quad-channel TLV4313 device is offered in a TSSOP-14 package.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TLV313	SC70 (5)	2.00 mm x 1.25 mm
ILVSIS	SOT23 (5)	2.90 mm × 1.60 mm
TLV2313	SOIC (8)	4.90 mm × 3.91 mm
1LV2313	VSSOP (8)	3.00 mm × 3.00 mm
TLV4313	TSSOP (14)	5.00 mm × 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Table of Contents

1	Features 1		8.3 Feature Description	17
2	Applications 1		8.4 Device Functional Modes	18
3	Description 1	9	Application and Implementation	19
4	Revision History2		9.1 Application Information	19
5	Device Comparison Table3		9.2 Typical Application	19
6	Pin Configuration and Functions		9.3 System Examples	20
7	Specifications6	10	Power Supply Recommendations	<mark>2</mark> 1
′	•		10.1 Input and ESD Protection	<mark>2</mark> 1
	7.1 Absolute Maximum Ratings	11	Layout	22
	7.3 Recommended Operating Conditions		11.1 Layout Guidelines	
	7.4 Thermal Information: TLV313		11.2 Layout Example	22
	7.5 Thermal Information: TLV2313	12	Device and Documentation Support	
	7.6 Thermal Information: TLV4313		12.1 Documentation Support	
	7.7 Electrical Characteristics: 5.5 V		12.2 Receiving Notification of Documentation Update	
	7.8 Electrical Characteristics: 1.8 V		12.3 Related Links	
	7.9 Typical Characteristics: Table of Graphs		12.4 Community Resources	23
	7.10 Typical Characteristics. Table of Graphs		12.5 Trademarks	
8	· · · · · · · · · · · · · · · · · · ·		12.6 Electrostatic Discharge Caution	23
0	Detailed Description 16 8.1 Overview 16		12.7 Glossary	23
	8.2 Functional Block Diagram	13	Mechanical, Packaging, and Orderable Information	

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Ci	hanges from Revision A (June 2016) to Revision B	Page
<u>.</u>	Changed pin assignment for DCK package	3
Cl	hanges from Original (June 2016) to Revision A	Page
•	Changed Product Status from Product Preview to Production Data	1
•	Changed the formatting of the Related Documentation section	23
•	Changed wording in the Receiving Notification of Documentation Updates section	23

Submit Documentation Feedback

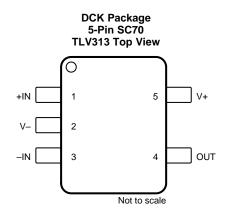
Copyright © 2016–2017, Texas Instruments Incorporated

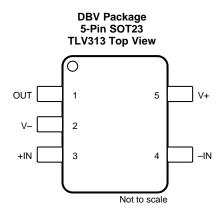


5 Device Comparison Table

	NO. OF			PACKAGE LEADS		
DEVICE	CHANNELS	SC70	SOT23	SOIC	VSSOP	TSSOP
TLV313	1	5	5	_	_	_
TLV2313	2	_	_	8	8	_
TLV4313	4	_	_	_	_	14

6 Pin Configuration and Functions



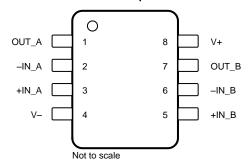


Pin Functions: TLV313

	Till Tullotions. TEVOTO					
	PIN			DESCRIPTION		
NAME	DCK (SC70)	DBV (SOT23)	I/O			
+IN	1	3	I	Noninverting input		
-IN	3	4	I	Inverting input		
OUT	4	1	0	Output		
V+	5	5	_	Positive (highest) power supply		
V-	2	2	_	Negative (lowest) power supply		



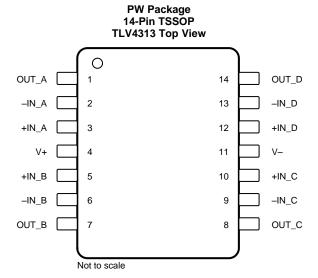




Pin Functions: TLV2313

	PIN				
NAME	D (SOIC)	DGK (VSSOP)	I/O	DESCRIPTION	
V-	4	4	_	Negative (lowest) power supply	
V+	8	8	_	Positive (highest) power supply	
OUT A	1	1	0	Output, channel A	
OUT B	7	7	0	Output, channel B	
-IN A	2	2	I	Inverting input, channel A	
+IN A	3	3	I	Noninverting input, channel A	
–IN B	6	6	I	Inverting input, channel B	
+IN B	5	5	I	Noninverting input, channel B	





Pin Functions: TLV4313

PIN		I/O	DESCRIPTION	
NAME	PW (TSSOP)	1,0	DESCRIPTION	
V-	11	_	Negative (lowest) power supply	
V+	4	_	Positive (highest) power supply	
OUT A	1	0	Output, channel A	
OUT B	7	0	Output, channel B	
OUT C	8	0	Output, channel C	
OUT D	14	0	Output, channel D	
−IN A	2	1	Inverting input, channel A	
+IN A	3	1	Noninverting input, channel A	
–IN B	6	I	Inverting input, channel B	
+IN B	5	1	Noninverting input, channel B	
-IN C	9	I	Inverting input, channel C	
+IN C	10	I	Noninverting input, channel C	
–IN D	13	I	Inverting input, channel D	
+IN D	12	I	Noninverting input, channel D	



7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
\	Supply voltage		7	V
Voltage	Signal input terminals ⁽²⁾	(V-) - (0.5)	(V+) + 0.5	V
Comment	Signal input terminals ⁽²⁾	-10	10	mA
Current	Output short circuit ⁽³⁾	Conti	Continuous	
	Operating, T _A	-40	150	°C
Temperature	Junction, T _J		150	°C
	Storage, T _{stg}	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Vs	Supply voltage	1.8	5.5	V
T_A	Specified temperature range	-40	125	°C

Product Folder Links: TLV313 TLV2313 TLV4313

⁽²⁾ Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.

⁽³⁾ Short-circuit to ground, one amplifier per package.

²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



7.4 Thermal Information: TLV313

		TLV		
	THERMAL METRIC ⁽¹⁾	DBV (SOT23)	DCK (SC70)	UNIT
		5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	228.5	281.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	99.1	91.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	54.6	59.6	°C/W
ΨЈТ	Junction-to-top characterization parameter	7.7	1.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	53.8	58.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

7.5 Thermal Information: TLV2313

		TLV	TLV2313		
	THERMAL METRIC ⁽¹⁾	D (SOIC)	DGK (VSSOP)	UNIT	
		8 PINS	8 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	138.4	191.2	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	89.5	61.9	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	78.6	111.9	°C/W	
ΨЈТ	Junction-to-top characterization parameter	29.9	5.1	°C/W	
ΨЈВ	Junction-to-board characterization parameter	78.1	110.2	°C/W	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W	

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

7.6 Thermal Information: TLV4313

		TLV4313	
	THERMAL METRIC ⁽¹⁾	PW (TSSOP)	UNIT
		14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	121.0	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	49.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	62.8	°C/W
ΨЈТ	Junction-to-top characterization parameter	5.9	°C/W
ΨЈВ	Junction-to-board characterization parameter	62.2	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

 For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

Product Folder Links: TLV313 TLV2313 TLV4313



7.7 Electrical Characteristics: 5.5 V

At T_A = 25°C, R_L = 10 k Ω connected to V_S / 2, and V_{CM} = V_{OUT} = V_S / 2, unless otherwise noted. (1)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET \	VOLTAGE		<u> </u>			
Vos	Input offset voltage			0.75	3	mV
dV _{OS} /dT	Input offset voltage vs temperature	$T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}$		2		μV/°C
PSRR	Power-supply rejection ratio		74	90		dB
INPUT VC	DLTAGE RANGE					
V _{CM}	Common-mode voltage range	No phase reversal, rail-to-rail input	(V-) - 0.2		(V+) + 0.2	V
CMRR	Cammon made rejection ratio	$(V_S-) - 0.2 \text{ V} < V_{CM} < (V_S+) - 1.3 \text{ V}$		85		dB
CIVIRR	Common-mode rejection ratio	$V_{CM} = -0.2 \text{ V to } 5.7 \text{ V}$	64	80		dB
INPUT BI	AS CURRENT		·			
I _B	Input bias current			±1		pA
I _{OS}	Input offset current			±1		pA
NOISE			·			
	Input voltage noise (peak-to- peak)	f = 0.1 Hz to 10 Hz		6		μV_{PP}
	Innut valtage paige density	f = 10 kHz		22		nV/√ Hz
e _n	Input voltage noise density	f = 1 kHz		26		nV/√ Hz
i _n	Input current noise density	f = 1 kHz		5		fA/√ Hz
INPUT CA	APACITANCE					
<u> </u>	Differential			1		pF
C _{IN}	Common-mode			5		pF
OPEN-LO	OP GAIN		·			
	Onen leen veltege gein	$0.05 \text{ V} < \text{V}_{\text{O}} < (\text{V+}) - 0.05 \text{ V}, \text{ R}_{\text{L}} = 100 \text{ k}\Omega$		104		dB
A _{OL}	Open-loop voltage gain	$0.3 \text{ V} < \text{V}_{\text{O}} < (\text{V+}) - 0.3 \text{ V}, \text{ R}_{\text{L}} = 2 \text{ k}\Omega$	100	110		dB
	Phase margin	V _S = 5.0 V, G = +1		65		0

⁽¹⁾ Parameters with minimum or maximum specification limits are 100% production tested at 25°C, unless otherwise noted. Overtemperature limits are based on characterization and statistical analysis.

Submit Documentation Feedback

Copyright © 2016–2017, Texas Instruments Incorporated



Electrical Characteristics: 5.5 V (continued)

At $T_A = 25$ °C, $R_L = 10 \text{ k}\Omega$ connected to $V_S / 2$, and $V_{CM} = V_{OUT} = V_S / 2$, unless otherwise noted. (1)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
FREQUE	ENCY RESPONSE					
GBW	Gain-bandwidth product	V _S = 5.0 V, C _L = 10 pF		1		MHz
SR	Slew rate	V _S = 5.0 V, G = +1		0.5		V/μs
ts	Settling time	To 0.01%, $V_S = 5.0 \text{ V}$, 2-V step , $G = +1$		6		μS
	Overload recovery time	$V_S = 5.0 \text{ V}, V_{IN} \times \text{Gain} > V_S$		3		μS
OUTPUT	Г					
	Voltage output swing from supply	$R_L = 100 \text{ k}\Omega^{(2)}$		5	20	mV
Vo	rails	$R_L = 2 k\Omega^{(2)}$		75	100	mV
I _{SC}	Short-circuit current			±15		mA
R _O	Open-loop output impedance			2300		Ω
POWER	SUPPLY					
Vs	Specified voltage range		1.8 (±0.9)		5.5 (±2.75)	V
IQ	Quiescent current per amplifier	$T_A = -40$ °C to 125°C, $V_S = 5.0$ V, $I_O = 0$ mA		65	90	μΑ
	Power-on time	V _S = 0 V to 5 V, to 90% I _Q level		10		μs

⁽²⁾ Specified by design and characterization; not production tested.

Product Folder Links: TLV313 TLV2313 TLV4313



7.8 Electrical Characteristics: 1.8 V

At $T_A = 25$ °C, $R_L = 10$ k Ω connected to V_S / 2, $V_{CM} = V_{S+} - 1.3$ V, and $V_{OUT} = V_S$ / 2, unless otherwise noted. (1)

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
OFFSET \	/OLTAGE				
Vos	Input offset voltage			0.75 3	mV
dV _{OS} /dT	Input offset voltage vs temperature	T _A = -40°C to 125°C		2	μV/°C
PSRR	Power-supply rejection ratio		74	90	dB
INPUT VC	LTAGE RANGE		·		
V _{CM}	Common-mode voltage range	No phase reversal, rail-to-rail input	(V-) - 0.2	(V+) + 0.2	V
CMDD	O-mana and an institute matin	$(V_S-) - 0.2 \text{ V} < V_{CM} < (V_S+) - 1.3 \text{ V}$		85	dB
CMRR	Common-mode rejection ratio	$V_{CM} = -0.2 \text{ V to } +1.8 \text{ V}$		73	dB
INPUT BI	AS CURRENT		<u>.</u>		
I _B	Input bias current			±1	pA
I _{OS}	Input offset current			±1	pА
NOISE			·		
	Input voltage noise (peak-to- peak)	f = 0.1 Hz to 10 Hz		6	μV_{PP}
_	I	f = 10 kHz		22	nV/√ Hz
e _n	Input voltage noise density	f = 1 kHz		26	nV/√Hz
i _n	Input current noise density	f = 1 kHz		5	fA/√Hz
INPUT CA	PACITANCE		<u> </u>		
0	Differential			1	pF
C _{IN}	Common-mode		5		pF
OPEN-LO	OP GAIN		·		•
	O	$0.1 \text{ V} < \text{V}_{\text{O}} < (\text{V+}) - 0.1 \text{ V}, \text{ R}_{\text{L}} = 10 \text{ k}\Omega$		110	dB
A _{OL}	Open-loop voltage gain	$0.05 \text{ V} < \text{V}_{\Omega} < (\text{V+}) - 0.05 \text{ V}, R_{L} = 100 \text{ k}\Omega$		110	dB

⁽¹⁾ Parameters with minimum or maximum specification limits are 100% production tested at 25°C, unless otherwise noted. Over-temperature limits are based on characterization and statistical analysis.

Submit Documentation Feedback

Copyright © 2016–2017, Texas Instruments Incorporated



Electrical Characteristics: 1.8 V (continued)

At $T_A = 25$ °C, $R_L = 10 \text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_{S+} - 1.3 \text{ V}$, and $V_{OUT} = V_S / 2$, unless otherwise noted. (1)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT		
SR Slew rate								
GBW	Gain-bandwidth product	C _L = 10 pF		0.9		MHz		
SR	Slew rate	G = +1		0.45		V/μs		
t _S	Settling time	To 0.01%, $V_S = 5.0 \text{ V}$, 2-V step , $G = +1$		6		μS		
	Overload recovery time	$V_S = 5.0 \text{ V}, V_{IN} \times \text{Gain} > V_S$		3		μS		
OUTPUT	T							
V	. Voltage output swing from supply	$R_L = 100 \text{ k}\Omega^{(2)}$		5		mV		
v _O	rails	$R_L = 2 k\Omega^{(2)}$		25		mV		
I _{SC}	Short-circuit current			±6		mA		
R _O	Open-loop output impedance			2300		Ω		
POWER	SUPPLY							
Vs	Specified voltage range		1.8 (±0.9)	5	5.5 (±2.75)	V		
IQ	Quiescent current per amplifier	$T_A = -40$ °C to 125°C, $V_S = 5.0$ V, $I_O = 0$ mA		65	90	μA		
	Power-on time	V _S = 0 V to 5 V, to 90% I _Q level		10		μs		

⁽²⁾ Specified by design and characterization; not production tested.

Product Folder Links: TLV313 TLV2313 TLV4313



7.9 Typical Characteristics: Table of Graphs

Table 1. Table of Graphs

TITLE	FIGURE
Open-Loop Gain and Phase vs Frequency	Figure 1
Quiescent Current vs Supply Voltage	Figure 2
Offset Voltage Production Distribution	Figure 3
Offset Voltage vs Common-Mode Voltage (Maximum Supply)	Figure 4
CMRR and PSRR vs Frequency (RTI)	Figure 5
0.1-Hz to 10-Hz Input Voltage Noise (5.5 V)	Figure 6
Input Voltage Noise Spectral Density vs Frequency (1.8 V, 5.5 V)	Figure 7
Input Bias and Offset Current vs Temperature	Figure 8
Open-Loop Output Impedance vs Frequency	Figure 9
Maximum Output Voltage vs Frequency and Supply Voltage	Figure 10
Output Voltage Swing vs Output Current (over Temperature)	Figure 11
Closed-Loop Gain vs Frequency, G = 1, −1, 10 (1.8 V)	Figure 12
Small-Signal Step Response, Noninverting (1.8 V)	Figure 13
Small-Signal Step Response, Noninverting (5.5 V)	Figure 14
Large-Signal Step Response, Noninverting (1.8 V)	Figure 15
Large-Signal Step Response, Noninverting (5.5 V)	Figure 16
No Phase Reversal	Figure 17
EMIRR IN+ vs Frequency	Figure 18

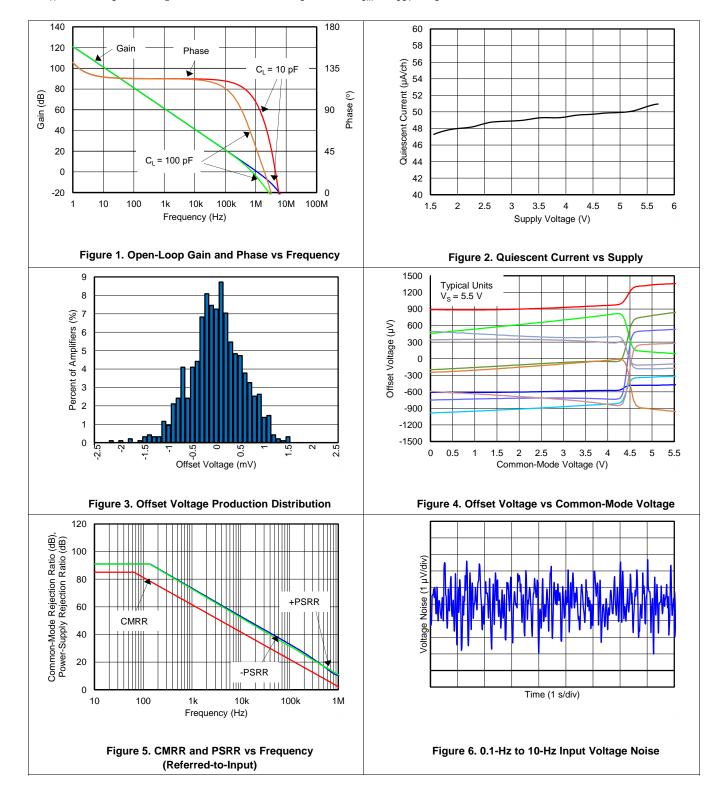
Submit Documentation Feedback

Copyright © 2016–2017, Texas Instruments Incorporated



7.10 Typical Characteristics

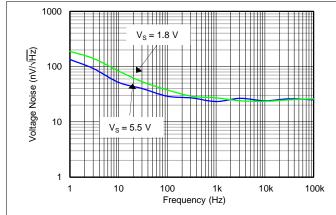
At $T_A = 25$ °C, $V_S = 5$ V, $R_L = 10$ k Ω connected to V_S / 2, and $V_{CM} = V_{OUT} = V_S$ / 2, unless otherwise noted.



TEXAS INSTRUMENTS

Typical Characteristics (continued)

At T_A = 25°C, V_S = 5 V, R_L = 10 k Ω connected to V_S / 2, and V_{CM} = V_{OUT} = V_S / 2, unless otherwise noted.



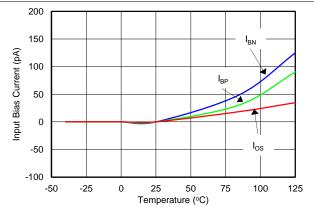
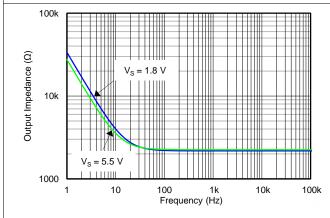


Figure 7. Input Voltage Noise Spectral Density vs Frequency

Figure 8. Input Bias and Offset Current vs Temperature



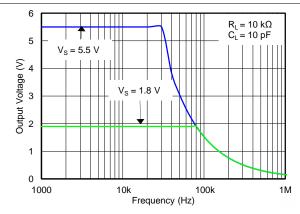
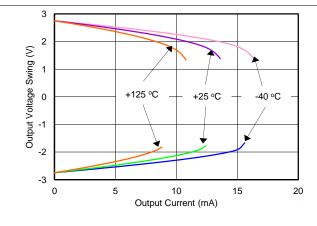


Figure 9. Open-Loop Output Impedance vs Frequency

Figure 10. Maximum Output Voltage vs Frequency and Supply Voltage



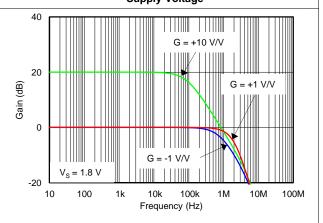


Figure 11. Output Voltage Swing vs Output Current (Over Temperature)

Figure 12. Closed-Loop Gain vs Frequency (Minimum Supply)

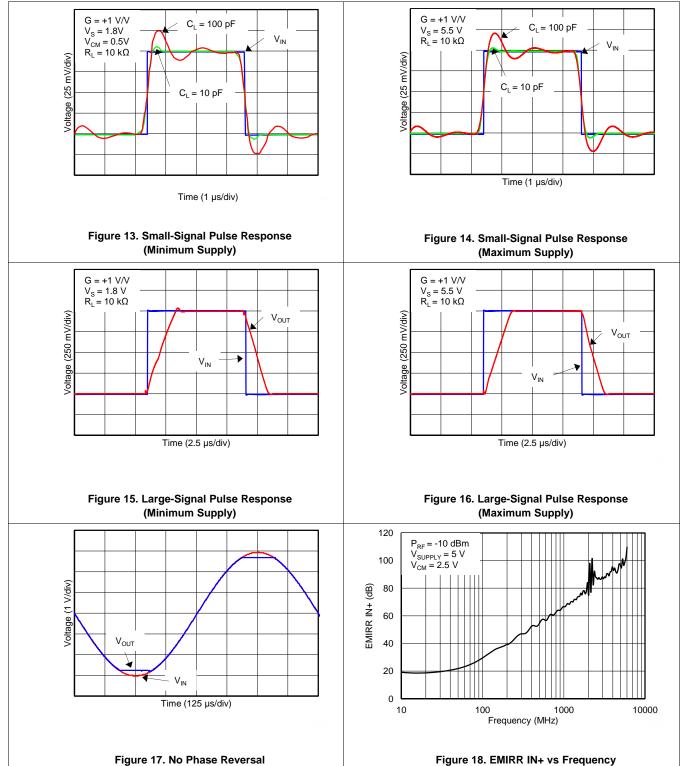
Submit Documentation Feedback

Copyright © 2016–2017, Texas Instruments Incorporated



Typical Characteristics (continued)

At $T_A = 25$ °C, $V_S = 5$ V, $R_L = 10$ k Ω connected to V_S / 2, and $V_{CM} = V_{OUT} = V_S$ / 2, unless otherwise noted.



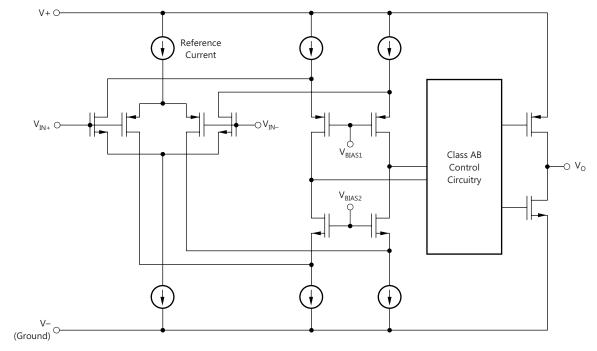


8 Detailed Description

8.1 Overview

The TLVx313 family of operational amplifiers are general-purpose devices that are ideal for a wide range of portable, low-cost applications. Rail-to-rail input and output swings, low quiescent current, and wide dynamic range make the op amps well-suited for driving sampling analog-to-digital converters (ADCs) as well as other single-supply applications.

8.2 Functional Block Diagram



Copyright © 2017, Texas Instruments Incorporated



8.3 Feature Description

8.3.1 Operating Voltage

The TLV313 series is fully specified and tested from 1.8 V to 5.5 V (±0.9 V to ±2.75 V). Parameters that vary with supply voltage are illustrated in the *Typical Characteristics* section.

8.3.2 Rail-to-Rail Input

The input common-mode voltage range of the TLV313 series extends 200 mV beyond the supply rails. This performance is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair, as shown in the *Functional Block Diagram* section. The N-channel pair is active for input voltages close to the positive rail, typically (V+) - 1.3 V to 200 mV above the positive supply, while the P-channel pair is on for inputs from 200 mV below the negative supply to approximately (V+) - 1.3 V. There is a small transition region, typically (V+) - 1.4 V to (V+) - 1.2 V, in which both pairs are on. This 200-mV transition region may vary up to 300 mV with process variation. Thus, the transition region (both stages on) may range from (V+) - 1.7 V to (V+) - 1.5 V on the low end, up to (V+) - 1.1 V to (V+) - 0.9 V on the high end. Within this transition region, PSRR, CMRR, offset voltage, offset drift, and THD may be degraded compared to device operation outside this region.

8.3.3 Rail-to-Rail Output

Designed as a micro-power, low-noise operational amplifier, the TLV313 device delivers a robust output drive capability. A class AB output stage with common-source transistors is used to achieve full rail-to-rail output swing capability. For resistive loads up to 100 k Ω , the output swings typically to within 5 mV of either supply rail regardless of the power-supply voltage applied. Different load conditions change the ability of the amplifier to swing close to the rails, as shown in Figure 12.

8.3.4 Common-Mode Rejection Ratio (CMRR)

CMRR for the TLV313 device is specified in several ways so the best match for a given application may be used; see the *Electrical Characteristics*. First, the CMRR of the device in the common-mode range below the transition region $[V_{CM} < (V+) - 1.3 \text{ V}]$ is given. This specification is the best indicator of the capability of the device when the application requires use of one of the differential input pairs. Second, the CMRR over the entire common-mode range is specified at $(V_{CM} = -0.2 \text{ V} \text{ to } 5.7 \text{ V})$. This last value includes the variations seen through the transition region, as shown in Figure 4.

8.3.5 Capacitive Load and Stability

The TLV313 device is designed to be used in applications where driving a capacitive load is required. As with all op amps, there may be specific instances where the TLV313 device may become unstable. The particular op amp circuit configuration, layout, gain, and output loading are some of the factors to consider when establishing whether or not an amplifier is stable in operation. An op amp in the unity-gain (+1-V/V) buffer configuration that drives a capacitive load exhibits a greater tendency to be unstable than an amplifier operated at a higher noise gain. The capacitive load, in conjunction with the op amp output resistance, creates a pole within the feedback loop that degrades the phase margin. The degradation of the phase margin increases as the capacitive loading increases. When operating in the unity-gain configuration, the TLV313 device remains stable with a pure capacitive load up to approximately 1 nF. The equivalent series resistance (ESR) of some capacitors (C_L greater than 1 μ F) is sufficient to alter the phase characteristics in the feedback loop such that the amplifier remains stable. Increasing the amplifier closed-loop gain allows the amplifier to drive increasingly larger capacitance. This increased capability is evident when observing the overshoot response of the amplifier at higher voltage gains.



Feature Description (continued)

One technique for increasing the capacitive load drive capability of the amplifier when it operates in a unity-gain configuration is to insert a small resistor, typically 10 Ω to 20 Ω , in series with the output, as shown in Figure 19. This resistor significantly reduces the overshoot and ringing associated with large capacitive loads. One possible problem with this technique is that a voltage divider is created with the added series resistor and any resistor connected in parallel with the capacitive load. The voltage divider introduces a gain error at the output that reduces the output swing.

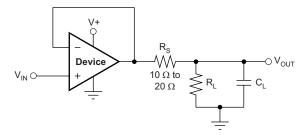


Figure 19. Improving Capacitive Load Drive

8.3.6 EMI Susceptibility and Input Filtering

Operational amplifiers vary with regard to the susceptibility of the device to electromagnetic interference (EMI). If conducted EMI enters the op amp, the dc offset observed at the amplifier output may shift from the nominal value while EMI is present. This shift is a result of signal rectification associated with the internal semiconductor junctions. While all op amp pin functions may be affected by EMI, the signal input pins are likely to be the most susceptible. The TLV313 family incorporates an internal input low-pass filter that reduces the amplifiers response to EMI. Both common-mode and differential mode filtering are provided by this filter. The filter is designed for a cutoff frequency of approximately 35 MHz (–3 dB), with a roll-off of 20 dB per decade.

Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10 MHz to 6 GHz. The EMI rejection ratio (EMIRR) metric allows op amps to be directly compared by the EMI immunity. Figure 18 illustrates the results of this testing on the TLV313 family. Detailed information may be found in *EMI Rejection Ratio of Operational Amplifiers* (SBOA128), available for download from www.ti.com.

8.4 Device Functional Modes

The TLV313 devices have a single functional mode. The devices are powered on as long as the power-supply voltage is between 1.8 V (\pm 0.9 V) and 5.5 V (\pm 2.75 V).



9 Application and Implementation

NOTE

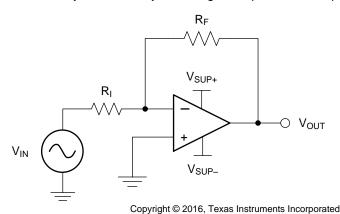
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TLVx313 devices are a family of low-power, rail-to-rail input and output operational amplifiers specifically designed for portable applications. The devices operate from 1.8 V to 5.5 V, are unity-gain stable, and are suitable for a wide range of general-purpose applications. The class AB output stage is capable of driving \leq 10-k Ω loads connected to any point between V+ and ground. The input common-mode voltage range includes both rails, and allows the TLV313 family to be used in virtually any single-supply application.

9.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier, as shown in Figure 20. An inverting amplifier takes a positive voltage on the input and outputs a signal inverted to the input, making a negative voltage of the same magnitude. In the same manner, the amplifier also makes negative input voltages positive on the output. In addition, amplification may be added by selecting the input resistor R_I and the feedback resistor R_F .



.

Figure 20. Application Schematic

9.2.1 Design Requirements

The supply voltage must be chosen to be larger than the input voltage range and the desired output range. The limits of the input common-mode range (V_{CM}) and the output voltage swing to the rails (V_O) must also be considered. For instance, this application scales a signal of ± 0.5 V (1 V) to ± 1.8 V (3.6 V). Setting the supply at ± 2.5 V is sufficient to accommodate this application.

9.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using Equation 1 and Equation 2:

$$A_{V} = \frac{V_{OUT}}{V_{IN}} \tag{1}$$

$$A_{V} = \frac{1.8}{-0.5} = -3.6 \tag{2}$$

Copyright © 2016–2017, Texas Instruments Incorporated



Typical Application (continued)

When the desired gain is determined, choose a value for R_I or R_F. Choosing a value in the kilohm range is desirable for general-purpose applications because the amplifier circuit uses currents in the milliamp range. This milliamp current range ensures the device does not draw too much current. The trade-off is that very large resistors (100s of kilohms) draw the smallest current but generate the highest noise. Small resistors (100s of ohms) generate low noise but draw high current. This example uses 10 k Ω for R_I, meaning 36 k Ω is used for R_F. The values are determined by Equation 3:

$$A_{V} = -\frac{R_{F}}{R_{I}} \tag{3}$$

9.2.3 Application Curve

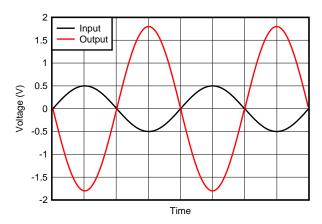
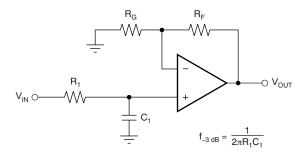


Figure 21. Inverting Amplifier Input and Output

9.3 System Examples

When receiving low-level signals, limiting the bandwidth of the incoming signals into the system is often required. The simplest way to establish this limited bandwidth is to place an RC filter at the noninverting terminal of the amplifier, as shown in Figure 22.



$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right) \left(\frac{1}{1 + sR_1C_1}\right)$$

Figure 22. Single-Pole Low-Pass Filter



System Examples (continued)

If even more attenuation is needed, a multiple pole filter is required. The Sallen-Key filter may be used for this task, as shown in Figure 23. For best results, the amplifier must have a bandwidth that is eight to 10 times the filter frequency bandwidth. Failure to follow this guideline may result in phase shift of the amplifier.

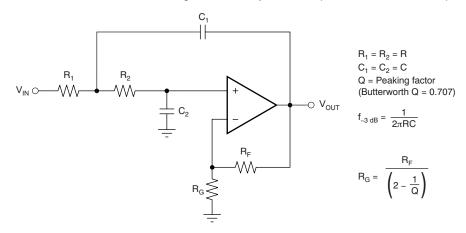


Figure 23. Two-Pole, Low-Pass, Sallen-Key Filter

10 Power Supply Recommendations

The TLVx313 family is specified for operation from 1.8 V to 5.5 V (±0.9 V to ±2.75 V); many specifications apply from -40°C to +125°C. The *Typical Characteristics* section presents parameters that may exhibit significant variance with regard to operating voltage or temperature.

CAUTION

Supply voltages larger than 7 V can permanently damage the device (see the *Absolute Maximum Ratings* table).

Place $0.1-\mu F$ bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, refer to the *Layout Guidelines* section.

10.1 Input and ESD Protection

The TLV313 family incorporates internal electrostatic discharge (ESD) protection circuits on all pins. In the case of input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. The ESD protection diodes also provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA as stated in the *Absolute Maximum Ratings*. Figure 24 shows how a series input resistor may be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

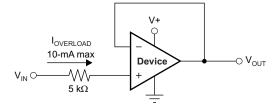


Figure 24. Input Current Protection



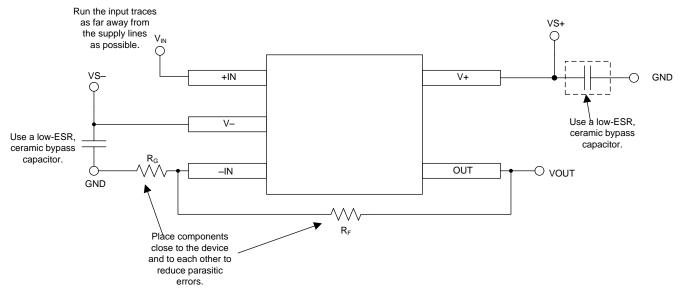
11 Layout

11.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise may propagate into analog circuitry through the power pins of the circuit and the operational amplifier. Use bypass capacitors to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most
 effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to
 ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Take care to
 physically separate digital and analog grounds, paying attention to the flow of the ground current. For
 more detailed information, refer to Circuit Board Layout Techniques, (SLOA089).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as
 possible. If the traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better
 than crossing in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keep R_F and R_G close to the inverting
 input in order to minimize parasitic capacitance, as shown in Figure 25.
- Keep the length of input traces as short as possible. Remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring may significantly reduce leakage currents from nearby traces that are at different potentials.

11.2 Layout Example



Copyright © 2016, Texas Instruments Incorporated

Figure 25. Operational Amplifier Board Layout for Noninverting Configuration

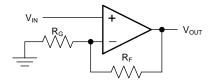


Figure 26. Schematic Representation of Figure 25

2 Submit Documentation Feedback

Copyright © 2016–2017, Texas Instruments Incorporated



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- EMI Rejection Ratio of Operational Amplifiers.
- Circuit Board Layout Techniques.

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on Alert me to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Related Links

PARTS

TLV313

TLV2313

TLV4313

Table 2 lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

TECHNICAL TOOLS & SUPPORT & SAMPLE & BUY PRODUCT FOLDER **SOFTWARE DOCUMENTS** COMMUNITY Click here Click here

Click here

Click here

Click here

Table 2. Related Links

12.4 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

Click here

TI E2E™ Online Community T's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.5 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

Click here

12.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.



ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.7 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

Copyright © 2016-2017, Texas Instruments Incorporated



13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

24 Submit Documentation Feedback Copyright © 2016-2017, Texas Instruments Incorporated

www.ti.com

2-Dec-2025

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
TLV2313IDGKR	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU SN NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	13AV
TLV2313IDGKR.A	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	13AV
TLV2313IDGKT	Active	Production	VSSOP (DGK) 8	250 SMALL T&R	Yes	NIPDAU SN NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	13AV
TLV2313IDGKT.A	Active	Production	VSSOP (DGK) 8	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	13AV
TLV2313IDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	V2313
TLV2313IDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	V2313
TLV313IDBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-2-260C-1 YEAR	-40 to 125	15F2
TLV313IDBVR.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	15F2
TLV313IDBVT	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	15F2
TLV313IDBVT.A	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	15F2
TLV313IDBVTG4	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	15F2
TLV313IDBVTG4.A	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	15F2
TLV313IDCKR	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	14E
TLV313IDCKR.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	14E
TLV313IDCKRG4	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	14E
TLV313IDCKRG4.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	14E
TLV313IDCKT	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	14E
TLV313IDCKT.A	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	14E
TLV4313IPWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU SN	Level-2-260C-1 YEAR	-40 to 125	TLV4313
TLV4313IPWR.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TLV4313

 $^{^{\}mbox{(1)}}$ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

PACKAGE OPTION ADDENDUM

www.ti.com 2-Dec-2025

(4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLV2313, TLV313:

Automotive: TLV2313-Q1, TLV313-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



www.ti.com 1-Nov-2025

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2313IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV2313IDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV2313IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV313IDBVR	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV313IDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV313IDBVTG4	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV313IDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV313IDCKR	SC70	DCK	5	3000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3
TLV313IDCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
TLV313IDCKRG4	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV313IDCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV313IDCKT	SC70	DCK	5	250	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
TLV4313IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



www.ti.com 1-Nov-2025



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2313IDGKR	VSSOP	DGK	8	2500	353.0	353.0	32.0
TLV2313IDGKT	VSSOP	DGK	8	250	353.0	353.0	32.0
TLV2313IDR	SOIC	D	8	2500	353.0	353.0	32.0
TLV313IDBVR	SOT-23	DBV	5	3000	208.0	191.0	35.0
TLV313IDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV313IDBVTG4	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV313IDCKR	SC70	DCK	5	3000	180.0	180.0	18.0
TLV313IDCKR	SC70	DCK	5	3000	208.0	191.0	35.0
TLV313IDCKR	SC70	DCK	5	3000	210.0	185.0	35.0
TLV313IDCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
TLV313IDCKT	SC70	DCK	5	250	180.0	180.0	18.0
TLV313IDCKT	SC70	DCK	5	250	210.0	185.0	35.0
TLV4313IPWR	TSSOP	PW	14	2000	356.0	356.0	35.0





NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side





NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.





NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.





NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale, TI's General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025